

Description

The K100N50X4B is high performance Aluminum Nitride (AIN) half flange termination intended as a cost competitive alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators, and for use in power combiners. The termination is also RoHS compliant!

General Specifications

Resistive Element Thick Film

Substrate AIN Ceramic

Mounting Flange Copper, nickel plated per QC-N-290

Operating Temperature -55°C to +150°C (see de rating chart)

Tolerance is ± 0.010 ", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions in inches.

Electrical Specifications

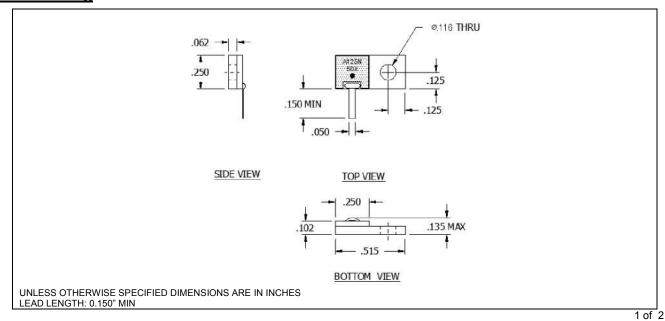
Resistance Value:50 Ohms, $\pm 2\%$ Power:100 WattsFrequency Range:DC -4.0 GHzReturn Loss> 26 dB to 1.3 GHz> 22 dB to 4.0 GHz

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change with out notice.**

Features:

- RoHS Compliant
- 100 Watts
- DC 4.0 GHz
- AIN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

Outline Drawing

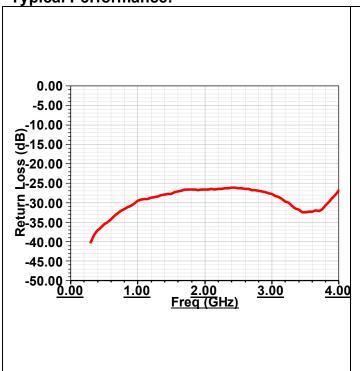


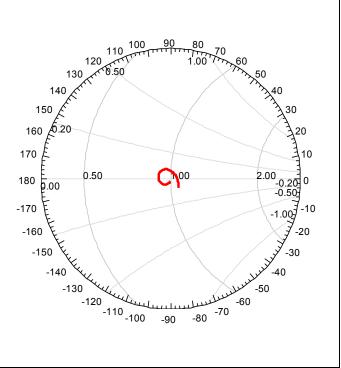


USA/Canada: (315) 432-8909 Toll Free: (800) 544-2414 Europe: +44 2392-232392

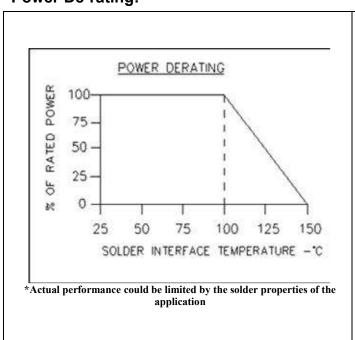


Typical Performance:

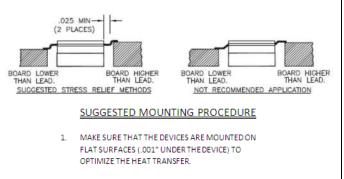




Power De-rating:



Mounting Footprint and Procedure:



- POSITION DEVICE ON MOUNTING SURFACE AND SOLDER IN PLACE USING AN APPROPRIATE SOLDER.
- SOLDER LEADS IN PLACE USING AN APPROPRIATE SOLDER TYPE WITH A CONTROLLED TEMPERATURE IRON.

2 of 2

